

HiPerFRED

 V_{RRM} 600 V

30 A

30 ns

High Performance Fast Recovery Diode Low Loss and Soft Recovery Parallel legs

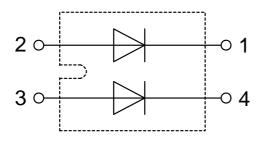
Part number

DSEP2x31-06B



Backside: isolated

F1 E72873



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: SOT-227B (minibloc)

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate: Copper
- internally DCB isolated
- Advanced power cycling

Terms Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747 and per semiconductor unless otherwise specified

20160920b

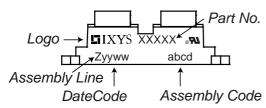


Fast Diode				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse blocki	ng voltage	$T_{VJ} = 25^{\circ}C$			600	V
V _{RRM}	max. repetitive reverse blocking vo	oltage	$T_{VJ} = 25^{\circ}C$			600	V
I _R	reverse current, drain current	$V_R = 600 \text{ V}$	$T_{VJ} = 25^{\circ}C$			250	μΑ
		$V_R = 600 V$	$T_{VJ} = 150$ °C			2	mΑ
V _F	forward voltage drop	I _F = 30 A	$T_{VJ} = 25^{\circ}C$			2.49	V
		$I_F = 60 A$				3.16	V
		I _F = 30 A	T _{VJ} = 150°C			1.59	V
		$I_F = 60 \text{ A}$				2.20	V
I _{FAV}	average forward current	T _c = 75°C	T _{VJ} = 150°C			30	Α
		rectangular d = 0.5					
V _{F0}	threshold voltage	and a decident and a	T _{VJ} = 150°C			1.01	V
\mathbf{r}_{F}	slope resistance	s calculation only				19.2	mΩ
R _{thJC}	thermal resistance junction to case	9				1.15	K/W
R _{thCH}	thermal resistance case to heatsin	ık			0.10		K/W
P _{tot}	total power dissipation		$T_C = 25^{\circ}C$			100	W
I _{FSM}	max. forward surge current	$t = 10 \text{ ms}$; (50 Hz), sine; $V_R = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			250	Α
C _J	junction capacitance	$V_R = 400 \text{V}$ f = 1 MHz	$T_{VJ} = 25^{\circ}C$		26		pF
I _{RM}	max. reverse recovery current		$T_{VJ} = 25 ^{\circ}\text{C}$		7.5		Α
		$I_F = 30 \text{ A}; V_R = 300 \text{ V}$	$T_{VJ} = 100 ^{\circ}\text{C}$		12.5		Α
t _{rr}	reverse recovery time	$\begin{cases} I_F = 30 \text{ A}; V_R = 300 \text{ V} \\ -di_F /dt = 400 \text{ A/µs} \end{cases}$	$T_{VJ} = 25 ^{\circ}\text{C}$		20		ns
	J	1	$T_{VJ} = 100^{\circ}C$		70		ns



Package SOT-227B (minibloc)			Ratings					
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal					100	Α
T _{VJ}	virtual junction temperature				-40		150	°C
Top	operation temperature				-40		125	°C
T _{stg}	storage temperature				-40		150	°C
Weight						30		g
M _D	mounting torque				1.1		1.5	Nm
$\mathbf{M}_{_{\mathbf{T}}}$	terminal torque				1.1		1.5	Nm
d _{Spp/App}	oroonogo diatanoo on ourfa	ce striking distance through air	terminal to terminal 10.5 terminal to backside 8.6		3.2			mm
d _{Spb/Apb}	creepage distance on sunat	ce striking distance through an			6.8			mm
V _{ISOL}	isolation voltage	t = 1 second			3000			V
.002	t = 1 minute		50/60 Hz, RMS; I _{ISOL} ≤ 1 mA		2500			V

Product Marking



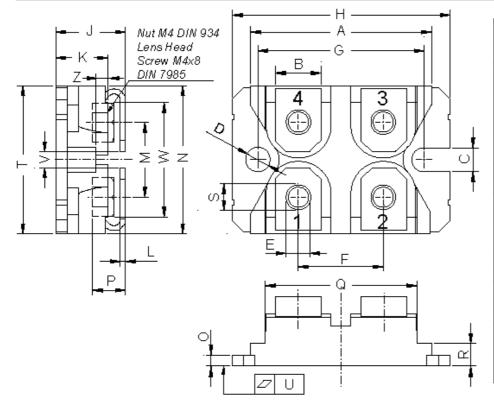
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEP2x31-06B	DSEP2x31-06B	Tube	10	476285

Similar Part	Package	Voltage class
DSEP2x31-06A	SOT-227B (minibloc)	600

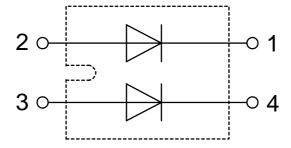
Equivalent Circuits for Simulation			* on die level	$T_{VJ} = 150 ^{\circ}\text{C}$
$I \rightarrow V_0$	R_0	Fast Diode		
V _{0 max}	threshold voltage	1.01		V
R_{0max}	slope resistance *	17.3		$m\Omega$



Outlines SOT-227B (minibloc)



Dim.	Millimeter		Inches		
DIM.	min	max	min	max	
Α	31.50	31.88	1.240	1.255	
В	7.80	8.20	0.307	0.323	
С	4.09	4.29	0.161	0.169	
D	4.09	4.29	0.161	0.169	
Е	4.09	4.29	0.161	0.169	
F	14.91	15.11	0.587	0.595	
G	30.12	30.30	1.186	1.193	
Н	37.80	38.23	1.488	1.505	
J	11.68	12.22	0.460	0.481	
K	8.92	9.60	0.351	0.378	
L	0.74	0.84	0.029	0.033	
M	12.50	13.10	0.492	0.516	
N	25.15	25.42	0.990	1.001	
0	1.95	2.13	0.077	0.084	
Р	4.95	6.20	0.195	0.244	
Q	26.54	26.90	1.045	1.059	
R	3.94	4.42	0.155	0.167	
S	4.55	4.85	0.179	0.191	
Т	24.59	25.25	0.968	0.994	
U	-0.05	0.10	-0.002	0.004	
V	3.20	5.50	0.126	0.217	
W	19.81	21.08	0.780	0.830	
Z	2.50	2.70	0.098	0.106	





Fast Diode

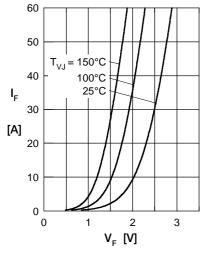


Fig. 1 Forward current I_F versus V_F

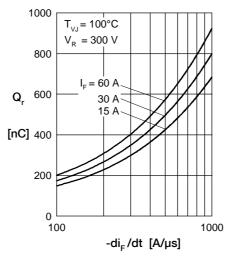


Fig. 2 Reverse recovery charge Q_r versus -di_F/dt

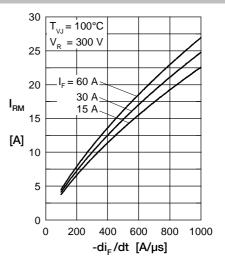


Fig. 3 Peak reverse current I_{RM} versus $-di_F/dt$

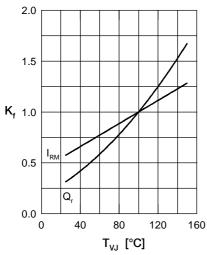


Fig. 4 Dynamic parameters Q_r , I_{RM} versus $T_{V.I}$

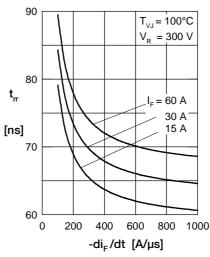


Fig. 5 Recovery time t_{rr} versus $-di_{F}/dt$

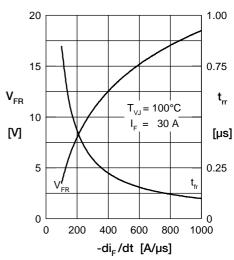


Fig. 6 Peak forward voltage V_{FR} and t_{fr} versus di_{F}/dt

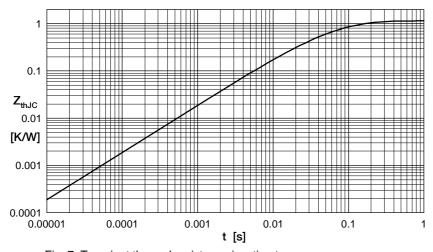


Fig. 7 Transient thermal resistance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t _i (s)
1	0.436	0.0055
2	0.482	0.0092
3	0.117	0.0007
4	0.115	0.0418

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Rectifiers category:

Click to view products by IXYS manufacturer:

Other Similar products are found below:

70HFR40 RL252-TP 150KR30A 1N5397 NTE5841 NTE6038 SCF5000 1N4002G 1N4005-TR JANS1N6640US 481235F
RRE02VS6SGTR 067907F MS306 70HF40 T85HFL60S02 US2JFL-TP A1N5404G-G ACGRA4007-HF ACGRB207-HF
CLH03(TE16L,Q) ACGRC307-HF ACEFC304-HF NTE6356 NTE6359 NTE6002 NTE6023 NTE6039 NTE6039 NTE6077 85HFR60 40HFR60
VS-88-7272PBF 70HF120 85HFR80 D126A45C SCF7500 D251N08B SCHJ22.5K SM100 SCPA2 SCH10000 SDHD5K VS12FL100S10 ACGRA4001-HF D1821SH45T PR D1251S45T NTE5990 NTE6358 NTE6162 NTE5998